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Exhibit 2: Akash GaN Transmitter

Akash is working to demonstrate a customized, compact Ka-band Akash Transmitter, which incorporates the Akash GaN-on-Diamond technology and a flight-proven software defined radio (SDR). Fig. 1 shows the Akash GaN MMIC, which will be integrated into the Akash Transmitter.

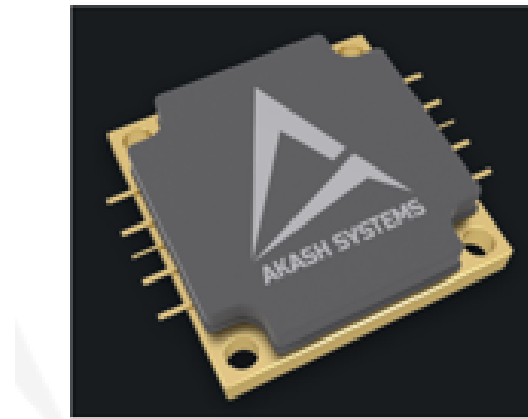


Figure 1. Akash GaN-on-Diamond MMIC technology

In simulations, the Transmitter is capable of data rates as high as 14 Gbps at 128 APSK modulation (dual polarization). Technical characteristics of the Akash GaN Transmitter are provided in Table 1.

Table 1. Akash GaN Transmitter Technical Characteristics

Operating Temperature	-24C to +65C
Operational Frequency	17 – 20 GHz
Drain Voltage	28 V
DC Power Consumption	156 W
Max RF Output Power	20 W
Dissipated Power at P_{linear}	136 W
Max Volume	30 x 20 x 10 cm
Max Mass	5 kg
Random Vibration	>14.1 Grms, 3-axis
Thermal Cycle	>23,000
Radiation Tolerance	100 krad (total dose chassis)
Latch-up	Immune
EEE Parts	Commercial space NASA Levels I, II, III; Military Grade B/S